

09-24-04

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ELM/002 Cont. 4

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Glenn J. Leedy
Application No. : 10/672,961 Confirmation No. : 9439
Filed : September 26, 2003
For : THREE DIMENSIONAL STRUCTURE INTEGRATED
CIRCUIT
Examiner : Not yet assigned
Group Art Unit : 2811

New York, New York 10020
September 23, 2004

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with 37 C.F.R. §§ 1.56 and 1.97,
applicants wish to call the attention of the Examiner to the
following documents:

U.S. Patent Documents

Foster	2,915,722	12/01/59
Farrand	3,202,948	08/24/65
Lesk	3,559,282	02/02/71
Burkhardt	3,560,364	02/02/71
Emmasingel	3,602,982	09/07/71
Medicus	3,615,901	10/26/71
Napoli et al.	3,716,429	02/13/73
Krishna et al.	3,777,227	12/14/73
Kuipers	3,868,565	02/25/75
Yerman	3,922,705	11/25/75
Wanlass	3,997,381	12/14/76
Stein	4,070,230	01/24/78

Greenwood et al.	4,131,985	01/02/79
Hauser, Jr. et al.	4,142,004	02/27/79
Hoeberechts	4,251,909	02/24/81
Kubacki	4,262,631	04/21/81
Shioya et al.	4,394,401	07/19/83
Trenkler et al.	4,401,986	08/30/83
Thomas et al.	4,416,054	11/22/83
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Schmitz	4,618,763	10/21/86
Christensen	4,663,559	05/05/87
Burns et al.	4,684,436	08/04/87
Hatada	4,693,770	09/15/87
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Mattox et al.	4,825,277	04/25/89
Tam et al.	4,857,481	08/15/89
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Sanders	5,273,940	12/28/93
Tuckerman	5,274,270	12/28/93
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Leedy	5,354,695	10/11/94
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Wang, et al.	RE 36,623	03/21/00
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"Miniature Electron Microscopes Without Vacuum Pumps, Self-Contained, Microfabricated Devices with Short Working Distances, Enable Operation in Air," *NASA Tech Briefs*, 39-40 (1998).

Partial European Search Report for Application No. EP 02009643 (October 8, 2002).

Copies of the aforementioned documents, which are listed on the accompanying Form PTO-1449 (submitted in duplicate), except U.S. patents and U.S. patent application publications (1276 OG 55), are enclosed herewith.

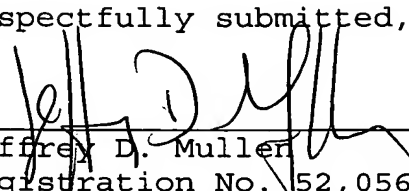
It is respectfully requested that these documents be (1) fully considered by the Patent and Trademark Office during examination of this application; and (2) printed on any patent which may issue on this application. Applicants request that a copy of Form PTO-1449, as considered and initialed by the Examiner, be returned with the next communication.

This Statement is being submitted more than three months from the application filing date but before the mailing date of the first Office Action on the merits.

In accordance with 37 C.F.R. § 1.97(b)(3), submission of this Statement requires no fee. However, if for any reason a fee is due, the Director is hereby authorized to charge payment of any fees required in connection with this Information Disclosure Statement to Deposit Account No. 06-1075. A duplicate copy of this statement is transmitted herewith.

An early and favorable action is respectfully
requested.

Respectfully submitted,



Jeffrey D. Muller
Registration No. 52,056
Agent for Applicants
Fish & Neave
Customer No. 1473
1251 Avenue of the Americas
New York, New York 10020
Tel.: (212) 596-9000
Fax: (212) 596-9090



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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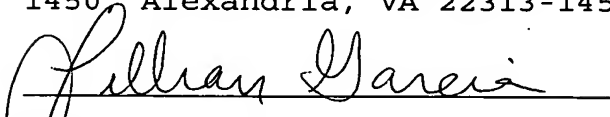
EXPRESS MAIL CERTIFICATION

"Express Mail" Mailing Label No. EL963273288US
Date of Deposit: September 23, 2004

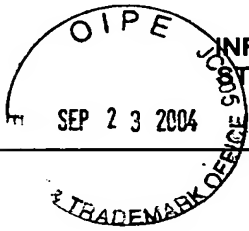
I hereby certify that this certification and the following papers and fees:

1. Information Disclosure Statement (in duplicate);
2. Form PTO-1449 (in duplicate);
3. Copies of forty-one (41) cited references; and
4. Return postcard

are being deposited with the United States Postal Service "EXPRESS MAIL POST OFFICE TO ADDRESSEE" service under 37 C.F.R. § 1.10 on the date indicated above and are addressed to Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.


Name: Lillian Garcia

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
ELM/002 Cont. 4APPLN. NO.
10/672,961APPLICANTS
Glenn J. LeedyCONF. NO.
9439FILING DATE
September 26, 2003GROUP ART UNIT
2811INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	2,915,722	12/01/59	Foster	336	115	
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	4,617,160	10/14/86	Belanger et al.	264	40.1	
	4,618,397	10/21/86	Shimizu et al.	156	628	
	4,618,763	10/21/86	Schmitz	250	211R	
	4,663,559	05/05/87	Christensen	313	336	

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	5,385,632	01/31/95	Goossen	156	630	
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	5,420,458	05/30/95	Shimoji	257	622	
	5,424,920	06/13/95	Miyake	361	735	
	5,426,072	06/20/95	Finnila	437	208	
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	5,432,729	07/11/95	Carson et al.	365	63	
	5,434,500	07/18/95	Hauck et al.	324	67	
	5,451,489	09/19/95	Leedy	430	313	
	5,453,404	09/26/95	Leedy	437	203	
	5,457,879	10/17/95	Gurtler et al.	29	895	
	5,476,813	12/19/95	Naruse	437	132	
	5,489,554	02/06/96	Gates	437	208	
	5,502,667	03/26/96	Bertin et al.	365	51	
	5,512,397	04/30/96	Leedy	430	30	
	5,527,645	06/18/96	Pati et al.	430	5	
	5,529,829	06/25/96	Koskenmaki et al.	428	167	
	5,534,465	07/09/96	Frye et al.	437	209	
	5,555,212	09/10/96	Toshiaki et al.	365	200	
	5,563,084	10/08/96	Ramm et al.	437	51	
	5,571,741	11/05/96	Leedy	437	51	
	5,580,687	12/03/96	Leedy	430	5	
	5,581,498	12/03/96	Ludwig et al.	365	63	
	5,582,939	12/10/96	Pierrat	430	5	

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	APPLICANTS Glenn J. Leedy	CONF. NO. 9439
	FILING DATE September 26, 2003	GROUP ART UNIT 2811

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	5,592,007	01/07/97	Leedy	257	347	
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	5,606,186	02/25/97	Noda	257	226	
	5,627,112	05/06/97	Tennant et al.	438	113	
	5,629,137	05/13/97	Leedy	430	313	
	5,633,209	05/27/97	Leedy	435	228	
	5,637,536	06/10/97	Val	438	686	
	5,654,127	08/05/97	Leedy	430	315	
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	5,675,185	10/07/97	Chen et al.	257	774	
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	5,750,211	05/12/98	Weise et al.	427	579	
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	5,773,152	06/30/98	Okonogi	428	446	
	5,786,116	07/28/98	Rolfson	430	5	
	5,793,115	08/11/98	Zavracky et al.	257	777	
	5,831,280	11/03/98	Ray	257	48	
	5,834,334	11/10/98	Leedy	438	107	
	5,840,593	11/24/98	Leedy	438	6	
	5,856,695	01/05/99	Ito et al.	257	370	
	5,868,949	02/09/99	Sotokawa et al.	216	18	
	5,869,354	02/09/99	Leedy	438	110	
	5,870,176	02/09/99	Sweatt et al.	355	53	
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	5,902,118	05/11/99	Hübner	438	106	
	5,915,167	06/22/99	Leedy	438	108	
	5,946,559	08/31/99	Leedy	438	157	
	5,985,693	11/16/99	Leedy	438	107	
	5,998,069	12/07/99	Cutter et al.	430	5	
	6,008,126	12/28/99	Leedy	438	667	
	6,020,257	02/01/00	Leedy	438	626	
	RE 36,623	03/21/00	Wang, et al.	427	579	
	6,045,625	04/04/00	Houston	148	33.3	
	6,084,284	07/04/00	Adamic, Jr.	257	506	
	6,087,284	07/11/00	Brix, et al.	501	69	
	6,097,096	08/01/00	Gardner et al.	257	777	
	6,133,640	10/17/00	Leedy	257	778	
	6,194,245 B1	02/27/01	Tayanaka	438	57	
	6,197,456 B1	03/06/01	Aleshin et al.	430	5	
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	6,236,602 B1	05/22/01	Patti	365	201	
	6,261,728 B1	07/17/01	Lin	430	30	
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	DE 32 33 195	03/1983	Germany				
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